

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	543	(438/719).CCLS.	USPAT	OR	OFF	2005/02/03 16:29
L4	482	(438/738).CCLS.	USPAT	OR	OFF	2005/02/03 16:29
L5	346	(438/743).CCLS.	USPAT	OR	OFF	2005/02/03 16:29
L6	0	(216/672).CCLS.	USPAT	OR	OFF	2005/02/03 16:29
L7	0	("(polysilicon adj gate) and etch and plasma and bromine and chlorine").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 16:30
L8	1811	(polysilicon adj gate) and etch and plasma and gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 16:30
L9	21	(polysilicon adj gate) and etch and plasma and gas and oxygen and Cl and Br and He	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 16:30
L10	548	(polysilicon adj gate) and etch and plasma and gas and RF	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 16:30
S1	727	(438/585).CCLS.	USPAT	OR	OFF	2005/02/03 13:14
S2	6	("6060345") or ("6174807") or ("6322714") or ("6342438") or ("6458671") or ("6479362").PN.	USPAT	OR	OFF	2005/02/03 16:28
S3	11	etch and (polysilicon adj gate) and (plasma adj reactor) and gas and (hard adj mask) and bromine and chlorine and oxygen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:19
S4	281	(438/584).CCLS.	USPAT	OR	OFF	2005/02/03 13:19